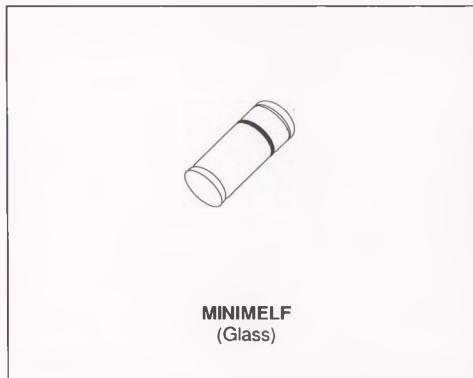


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

General purpose, metal to silicon diode featuring high breakdown voltage low turn-on voltage.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		100	V
I_F	Forward Continuous Current	$T_J = 25^\circ\text{C}$	150	mA
I_{FRM}	Repetitive Peak Forward Current	$t_p \leq 1\text{s}$ $\delta \leq 0.5$	350	mA
I_{FSM}	Surge non Repetitive Forward Current	$t_p = 10\text{ms}$	750	mA
P_{tot}	Power Dissipation	$T_J = 80^\circ\text{C}$	150	mW
T_{stg} T_J	Storage and Junction Temperature Range		- 65 to 150 - 65 to 125	$^\circ\text{C}$ $^\circ\text{C}$
T_L	Maximum Temperature for Soldering during 15s		260	$^\circ\text{C}$

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction-leads	300	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$V_{(BR)}$	$T_j = 25^\circ\text{C}$	$I_R = 100\mu\text{A}$	100			V
V_F^*	$T_j = 25^\circ\text{C}$	$I_F = 0.1\text{mA}$			0.25	V
	$T_j = 25^\circ\text{C}$	$I_F = 10\text{mA}$			0.45	
	$T_j = 25^\circ\text{C}$	$I_F = 250\text{mA}$			1	
I_R^*	$T_j = 25^\circ\text{C}$	$V_R = 1.5\text{V}$			0.5	μA
	$T_j = 60^\circ\text{C}$				5	
	$T_j = 25^\circ\text{C}$	$V_R = 10\text{V}$			0.8	
	$T_j = 60^\circ\text{C}$				7.5	
	$T_j = 25^\circ\text{C}$	$V_R = 50\text{V}$			2	
	$T_j = 60^\circ\text{C}$				15	
	$T_j = 25^\circ\text{C}$	$V_R = 75\text{V}$			5	
	$T_j = 60^\circ\text{C}$				20	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	$T_j = 25^\circ\text{C}$	$V_R = 0\text{V}$		10		μF
	$T_j = 25^\circ\text{C}$	$V_R = 1\text{V}$		6		

* Pulse test : $t_p \leq 300\mu\text{s}$ $\delta < 2\%$

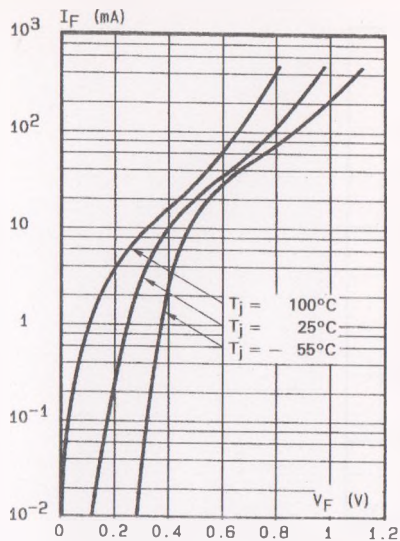


Fig.1 - Forward current versus forward voltage at different temperatures (typical values).

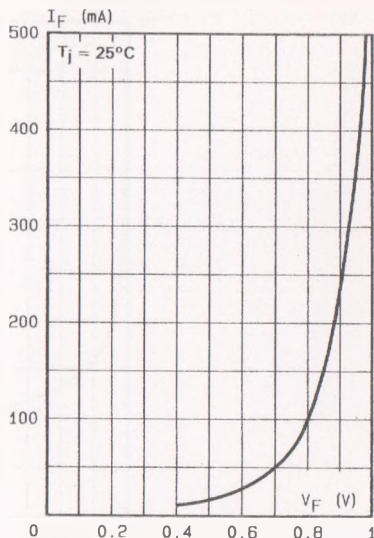


Fig.2 - Forward current versus forward voltage (typical values).

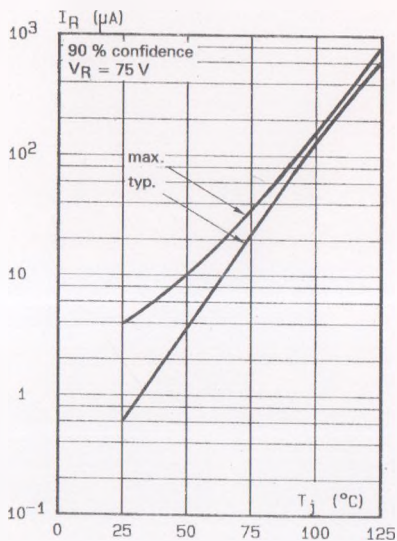


Fig.3 - Reverse current versus junction temperature (typical values).

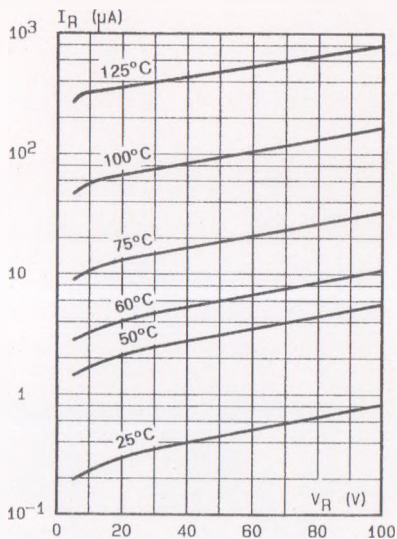


Fig.4 - Reverse current versus continuous reverse voltage

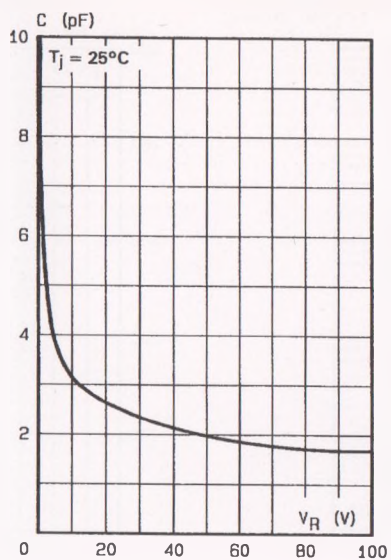


Fig.5 - Capacitance C versus reverse applied voltage V_R (typical values).